Topics

- Layout Styles
- Layout Strategies

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3D Perspective



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Design Rules

- Interface between designer and process engineer
- Guidelines for constructing process masks
- Unit dimension: Minimum line width
 - scalable design rules: lambda parameter
 - absolute dimensions (micron rules)

CMOS Process Layers

Layer	Color	Representation
Well (p,n)	Yellow	
Active Area (n+,p+)	Green	
Select (p+,n+)	Green	C
Polysilicon	Red	
Metal1	Blue	
Metal2	Magenta	
Contact To Poly	Black	
Contact To Diffusion	Black	
Via	Black	

Layers in 0.25 µm CMOS process



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Horizontal flow (vertical transistors)



Layout Styles

Horizontal flow (horizontal transistors)



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Layout Styles

- Vertical flow (horizontal transistors)
- Standard cell design



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Wiring Tracks

- A wiring track is the space required for a wire - 4λ width, 4λ spacing from neighbor = 8λ pitch
- Transistors also consume one wiring track



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Well spacing

- Wells must surround transistors by 6 λ
 - Implies 12 λ between opposite transistor flavors
 - Leaves room for one wire track



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Area Estimation

Estimate area by counting wiring tracks



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Example: O3AI



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- How do you decide on a layout?
 - Area constraints
 - Requirements of inputs and outputs
 - Metal layer interconnect
 - Difficult for multi-input gates
 - How do you decide on order of inputs?

- Euler path method
- Convert schematic into a graph
- Eg. F=AB+C+DE





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•A to B to C to D to E

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- Euler path method
 - Not always guaranteed to find a Euler path
 - For example, if the function was
 F=C+AB+DE
 - If no Euler path found, you will need to break the gate, or rearrange the inputs

- How do you decide on a layout?
 - Area constraints
 - Requirements of inputs and outputs
 - Metal layer interconnect
 - Performance considerations

- Very wide transistors
 - Multiple contacts to reduce diffusion resistance
 - Folding to reduce diffusion capacitance

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- Performance implications
 - Number of transistors at output
 - Order of transistors

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which will decrease switching time

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Move higher capacitances closer to ground and away from output

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Merged drain at A&B may cause the gate to become wider

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•Ordering of inputs



- If A arrives before B, it will charge up the capacitance to VDD. When B arrives, it needs to discharge the capacitor.
- If B arrives before A, the capacitor will be discharged before A arrives.
- Try and put the early arriving signal close to ground can speed NAND up to 20%

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Layout Choices

- Horizontal transistors
 - When FET sizes are similar
 - When data is in a vertical flow
- Vertical transistors
 - Different size FETs
 - Horizontal data flow
 - More complex functions

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Layout choices



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Layout choices

- Interconnect
 - Keep VDD and VSS in the highest level metal
 - Within a single cell, use a single layer of metal so you can route other metal layers above the cell
 - Limit the use of vias can be up to 50Ω per via
 - Don't have long runs of poly

Layout choices

- Consider how low level cells will interconnect with each other
- Minimize locally and compact globally
- Find critical areas first and then optimize

Layout Process

- Design Rule Check (DRC)
 - Check if all design rules are met
- Layout vs. Schematic (LVS)
 - Make sure that the layout matches your schematic

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Next class

- Exam 1
- Power Dissipation
- Final Project

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